



# Advance Information

## Single IGBT High Current Gate Driver

The MC33154 is specifically designed as an IGBT driver for high powered applications including ac induction motor control, brushless dc motor control, and uninterruptable power supplies. This device also offers a cost effective solution for driving power MOSFETS and Bipolar transistors.

Device protections include the choice of desaturation or overcurrent sensing and an undervoltage lockout to provide assurance of proper gate drive voltage.

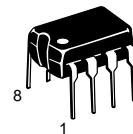
These devices are available in dual-in-line and surface mount packages and include the following features:

- High Current Output Stage: 4.0 A Source –2.0 A Sink
- Protection Circuits for Both Conventional and Sense IGBT's
- Current Source for Blanking Timing
- Protection Against Over-Current and Short Circuit
- Under-Voltage Lockout Optimized for IGBT's
- Negative Gate Drive Capability

# MC33154

## SINGLE IGBT HIGH CURRENT GATE DRIVER

### SEMICONDUCTOR TECHNICAL DATA

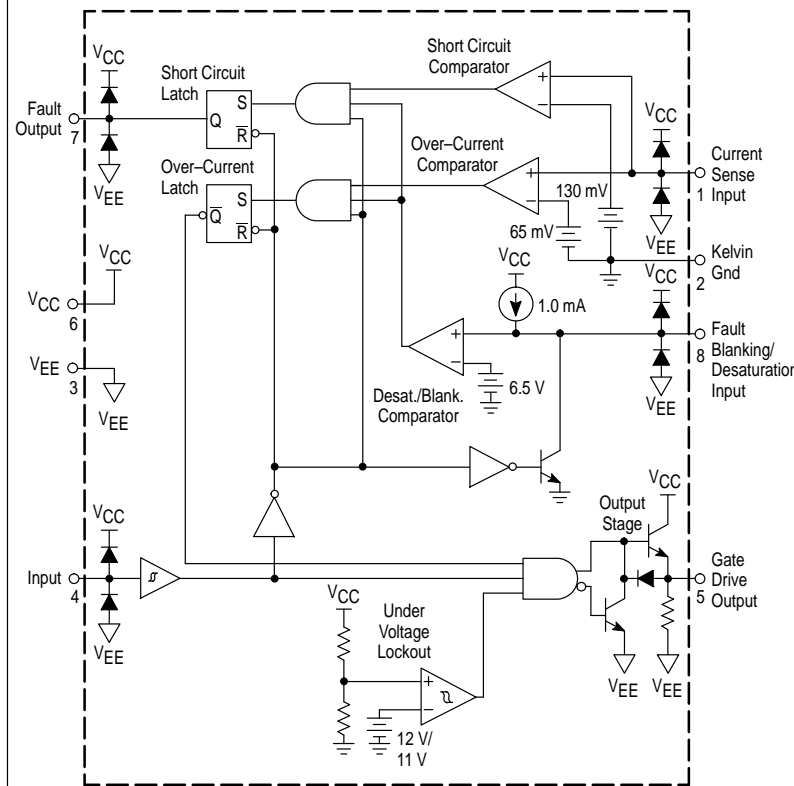


**P SUFFIX**  
PLASTIC PACKAGE  
CASE 626

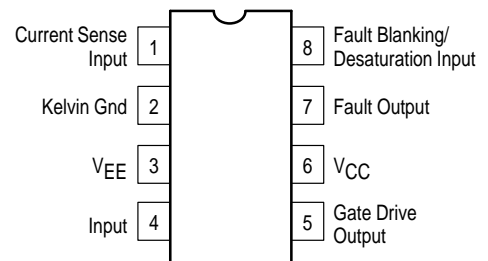


**D SUFFIX**  
PLASTIC PACKAGE  
CASE 751  
(SO-8)

### Simplified Block Diagram



### PIN CONNECTIONS



### ORDERING INFORMATION

| Device   | Tested Operating Temperature Range | Package       |
|----------|------------------------------------|---------------|
| MC33154D | T <sub>A</sub> = -40° to +85°C     | Plastic SO-8  |
| MC33154P | T <sub>A</sub> = -40° to +85°C     | Plastic DIP-8 |

# MC33154

## MAXIMUM RATINGS

| Rating   | Symbol   | Value                                    | Unit                       |
|--|--|--|----------------------------|
| Power Supply Voltage<br>V <sub>CC</sub> to V <sub>EE</sub> ; V <sub>EE</sub> ≤ KGND ≤ V <sub>CC</sub><br>Kelvin Ground to V <sub>EE</sub> (Note 1)   | V <sub>CC</sub> - V <sub>EE</sub><br>KGnd - V <sub>EE</sub>                  | 20<br>20                                 | V                          |
| Input  | V <sub>in</sub>  | V <sub>EE</sub> - 0.3 to V <sub>CC</sub> | V                          |
| Current Sense Input  | V <sub>CS</sub>  | -0.3 to V <sub>CC</sub>                  | V                          |
| Fault Blanking/Desaturation Input  | V <sub>BD</sub>  | -0.3 to V <sub>CC</sub>                  | V                          |
| Gate Drive Output<br>Source Current<br>Sink Current<br>Diode Clamp Current   | I <sub>O</sub>   | 4.0<br>2.0<br>1.0                        | A                          |
| Fault Output<br>Source Current<br>Sink Current   | I <sub>FO</sub>  | 25<br>10                                 | mA                         |
| Power Dissipation and Thermal Characteristics<br>D Suffix SO-8 Package, Case 751<br>Maximum Power Dissipation @ T <sub>A</sub> = 50°C<br>Thermal Resistance, Junction-to-Air<br>P Suffix DIP-8 Package, Case 626<br>Maximum Power Dissipation @ T <sub>A</sub> = 50°C<br>Thermal Resistance, Junction-to-Air | P <sub>D</sub><br>R <sub>θJA</sub><br><br>P <sub>D</sub><br>R <sub>θJA</sub> | 0.56<br>180<br><br>1.0<br>100            | W<br>°C/W<br><br>W<br>°C/W |
| Operating Junction Temperature   | T <sub>J</sub>   | 150                                      | °C                         |
| Operating Ambient Temperature  | T <sub>A</sub>   | -40 to +85                               | °C                         |
| Storage Temperature Range  | T <sub>stg</sub>   | -65 to +150                              | °C                         |

**NOTES:** 1. Kelvin Ground must always be between V<sub>EE</sub> and V<sub>CC</sub>.  
2. ESD data available upon request.

**ELECTRICAL CHARACTERISTICS** (V<sub>CC</sub> = 20 V, V<sub>EE</sub> = 0 V, Kelvin Gnd connected to V<sub>EE</sub>. For typical values T<sub>A</sub> = 25°C, for min/max values T<sub>A</sub> is the operating ambient temperature range that applies [Note 1] unless otherwise noted.)

| Characteristic   | Symbol   | Min     | Typ         | Max               | Unit |
|--|--|---------|-------------|-------------------|------|
| <b>INPUT</b>   |  |         |             |                   |      |
| Input Threshold Voltage<br>High State (Logic 1) @ T <sub>A</sub> = 25°C<br>@ T <sub>A</sub> = -40 to +85°C<br>Low State (Logic 0)          | V <sub>IH</sub><br><br>V <sub>IL</sub>                 |         | 9.0<br>7.0  | 10.5<br>11.6<br>- | V    |
| Input Current — High State (V <sub>IH</sub> = 10.5 V)<br>— Low State (V <sub>IL</sub> = 4.5 V)   | I <sub>IH</sub><br>I <sub>IL</sub>                     | -<br>-  | 100<br>50   | 500<br>100        | μA   |
| <b>GATE DRIVE OUTPUT</b>   |  |         |             |                   |      |
| Output Voltage<br>Low State (I <sub>Sink</sub> = 1.0 A)<br>High State (I <sub>Source</sub> = 2.0 A)  | V <sub>OL</sub><br>V <sub>OH</sub>                     | -<br>17 | 2.0<br>18   | 2.5<br>-          | V    |
| Output Pull-Down Resistor  | R <sub>PD</sub>  | -       | 100         | 200               | kΩ   |
| <b>FAULT OUTPUT</b>  |  |         |             |                   |      |
| Output Voltage<br>Low State (I <sub>Sink</sub> = 5.0 mA)<br>High State (I <sub>Source</sub> = 20 mA)                                       | V <sub>FL</sub><br>V <sub>FH</sub>                     | -<br>17 | 0.2<br>18.3 | 1.0<br>-          | V    |
| <b>SWITCHING CHARACTERISTICS</b>   |  |         |             |                   |      |
| Propagation Delay (50% Input to 50% Output C <sub>L</sub> = 15 nF)<br>Logic Input to Drive Output Rise<br>Logic Input to Drive Output Fall | t <sub>PLH</sub> (in/out)<br>t <sub>PHL</sub> (in/out) | -<br>-  | 200<br>120  | 300<br>300        | ns   |
| Drive Output Rise Time (10% to 90%) C <sub>L</sub> = 15 nF   | t <sub>r</sub>   | -       | 80          | 200               | ns   |
| Drive Output Fall Time (90% to 10%) C <sub>L</sub> = 15 nF   | t <sub>f</sub>   | -       | 80          | 200               | ns   |
| Propagation Delay<br>Current Sense Input to Drive Output   | t <sub>P(OC)</sub>                                     | -       | 0.4         | 1.0               | μs   |

**NOTE:** 1. Low duty cycle pulse techniques are used during test to maintain the junction temperature as close to ambient as possible.  
T<sub>low</sub> = -40°C for MC33154      T<sub>high</sub> = +85°C for MC33154

# MC33154

**ELECTRICAL CHARACTERISTICS (continued)** ( $V_{CC} = 20\text{ V}$ ,  $V_{EE} = 0\text{ V}$ , Kelvin Gnd connected to  $V_{EE}$ . For typical values  $T_A = 25^\circ\text{C}$ , for min/max values  $T_A$  is the operating ambient temperature range that applies [Note 1] unless otherwise noted.)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

## SWITCHING CHARACTERISTICS

|   |              |   |     |     |  |
|---|--------------|---|-----|-----|--|
| Fault Blanking/Desaturation Input to Drive Output | $t_{P(FLT)}$ | – | 0.4 | 1.0 |  |
|---|--------------|---|-----|-----|--|

## UVLO

|                  |                       |      |    |      |   |
|------------------|-----------------------|------|----|------|---|
| Start-up Voltage | $V_{CC\text{ start}}$ | 11.3 | 12 | 12.6 | V |
| Disable Voltage  | $V_{CC\text{ dis}}$   | 10.4 | 11 | 11.7 | V |

## COMPARATORS

|  |               |     |      |     |               |
|--|---------------|-----|------|-----|---------------|
| Over Current Trip Voltage ( $V_{Pin8} > 7.0\text{ V}$ )  | $V_{SOC}$     | 50  | 65   | 80  | mV            |
| Short Current Trip Voltage ( $V_{Pin8} > 7.0\text{ V}$ ) | $V_{SSC}$     | 100 | 130  | 160 | mV            |
| Desaturation Threshold ( $V_{Pin1} > 100\text{ mV}$ )    | $V_{th(FLT)}$ | 6.0 | 6.5  | 7.0 | V             |
| Sense Input Current ( $V_{SI} = 0\text{ V}$ )            | $I_{SI}$      | –   | –1.4 | –10 | $\mu\text{A}$ |

## FAULT BLANKING/DESATURATION INPUT

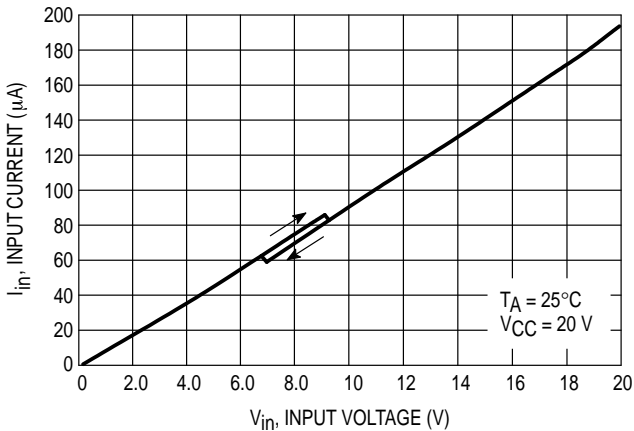
|  |             |     |     |     |    |
|--|-------------|-----|-----|-----|----|
| Current Source ( $V_{Pin8} = 0\text{ V}$ , $V_{Pin4} \geq 10.5\text{ V}$ ) | $I_{chg}$   | 0.8 | 1.0 | 1.2 | mA |
| Discharge Current ( $V_{Pin8} = 15\text{ V}$ , $V_{Pin4} = 0\text{ V}$ )   | $I_{dschg}$ | 0.8 | 2.5 | –   | mA |

## TOTAL DEVICE

|   |          |   |     |    |    |
|---|----------|---|-----|----|----|
| Power Supply Current<br>Standby ( $V_{Pin\ 4} = 0\text{ V}$ , Output Open)<br>Operating ( $C_L = 15\text{ nF}$ , $f_{in} = 20\text{ kHz}$ ) | $I_{CC}$ | – | 9.0 | 14 | mA |
|   |          | – | 15  | 25 |    |

**NOTE:** 1. Low duty cycle pulse techniques are used during test to maintain the junction temperature as close to ambient as possible.  
 $T_{low} = -40^\circ\text{C}$  for MC33154       $T_{high} = +85^\circ\text{C}$  for MC33154

**Figure 1. Input Current versus Logic Input Voltage**



**Figure 2. Output Voltage versus Input Voltage**

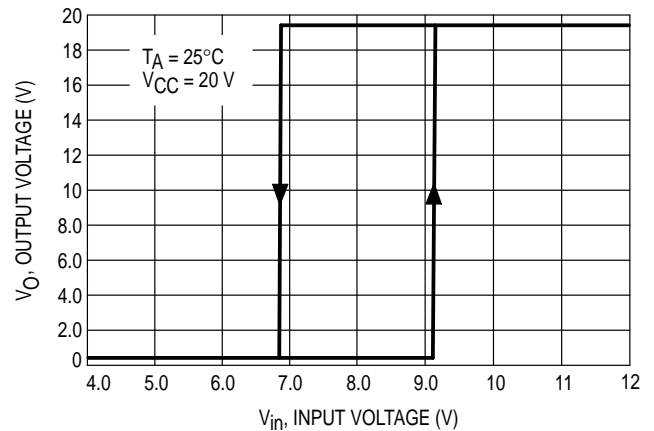


Figure 3. Input Threshold Voltage versus Supply Voltage

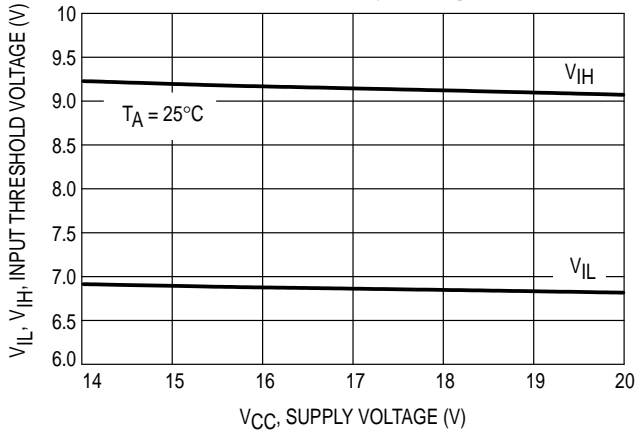


Figure 4. Input Thresholds versus Temperature

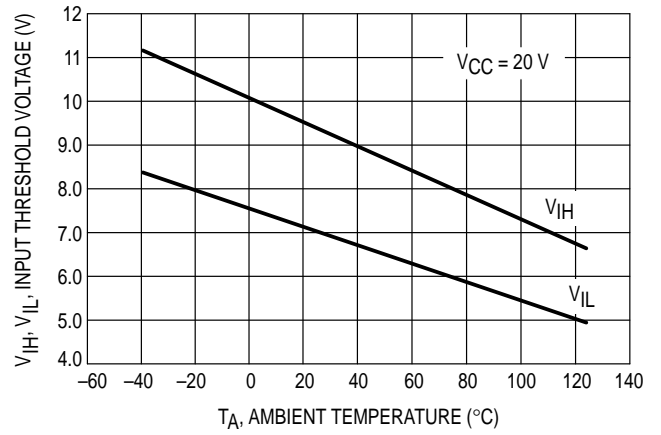


Figure 5. Drive Output Low State Voltage versus Temperature

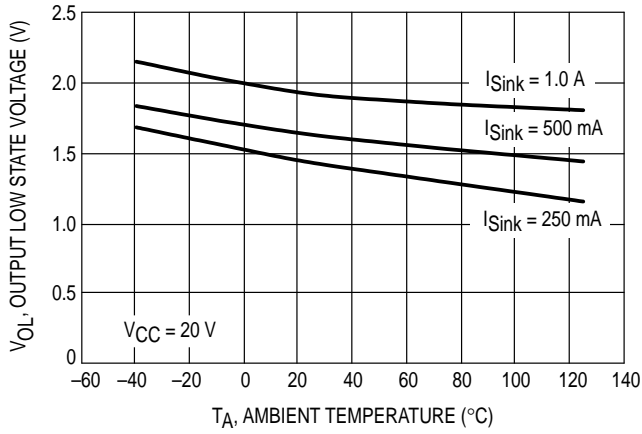


Figure 6. Drive Output Low State Voltage versus Sink Current

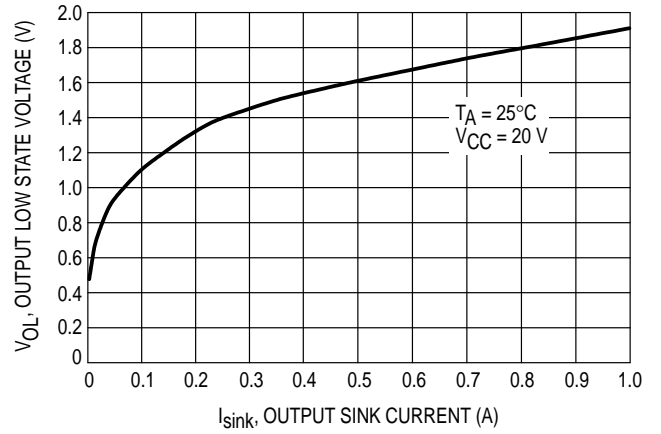


Figure 7. Drive Output High State Voltage versus Temperature

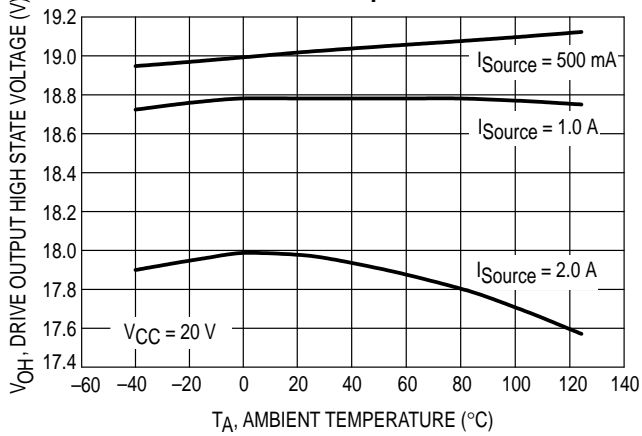
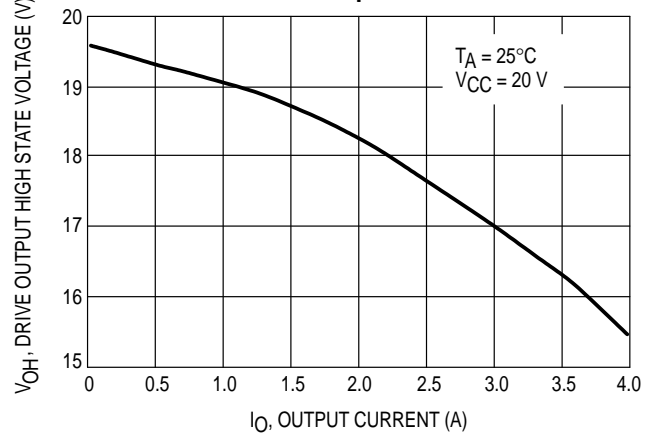
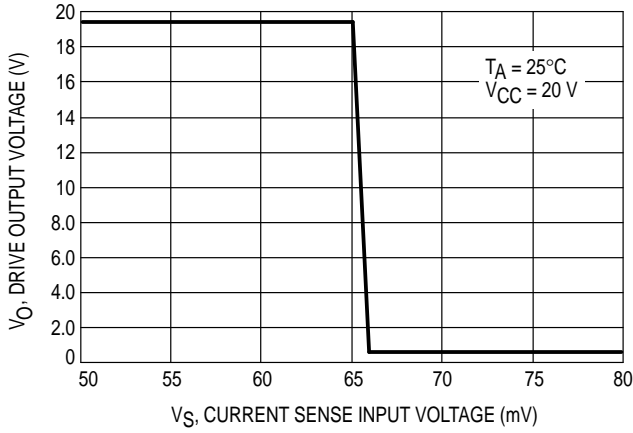


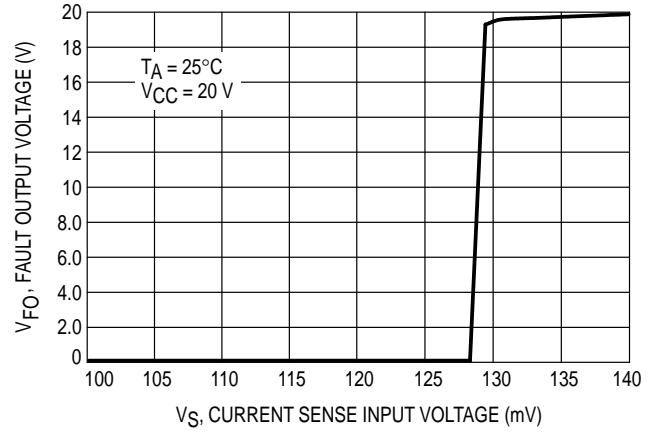
Figure 8. Output Saturation High versus Output Current



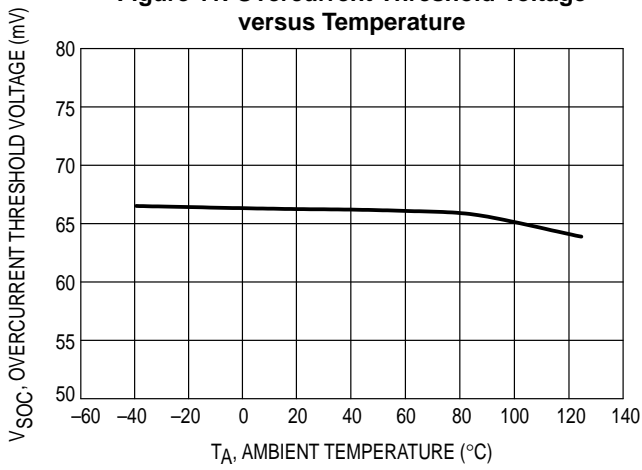
**Figure 9. Drive Output Voltage versus Current Sense Input Voltage**



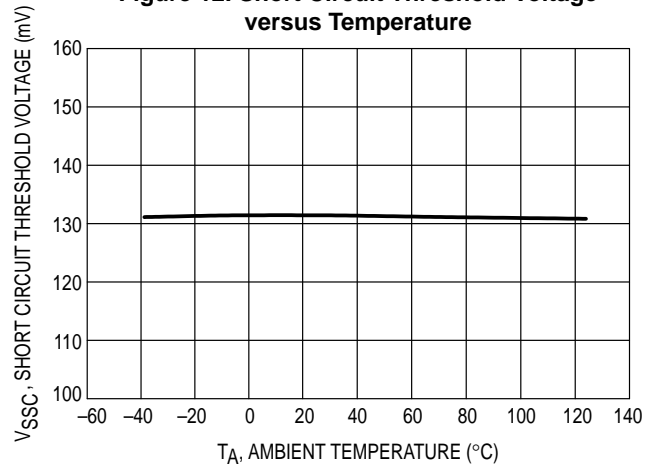
**Figure 10. Fault Output Voltage versus Current Sense Input Voltage**



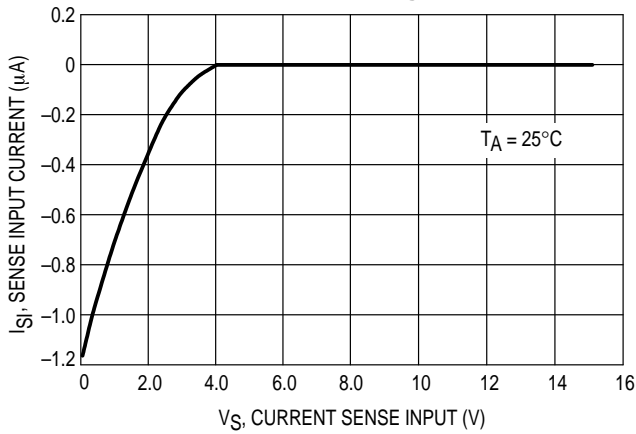
**Figure 11. Overcurrent Threshold Voltage versus Temperature**



**Figure 12. Short Circuit Threshold Voltage versus Temperature**



**Figure 13. Sense Input Current versus Sense Voltage**



**Figure 14. Output Voltage versus Blanking/Desaturation Voltage**

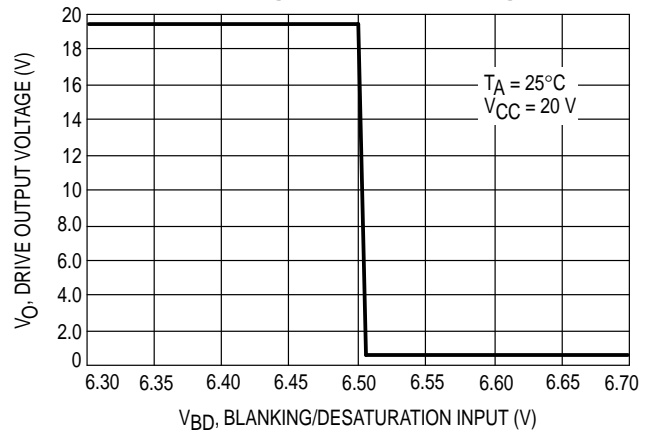


Figure 15. Desaturation Threshold versus Temperature

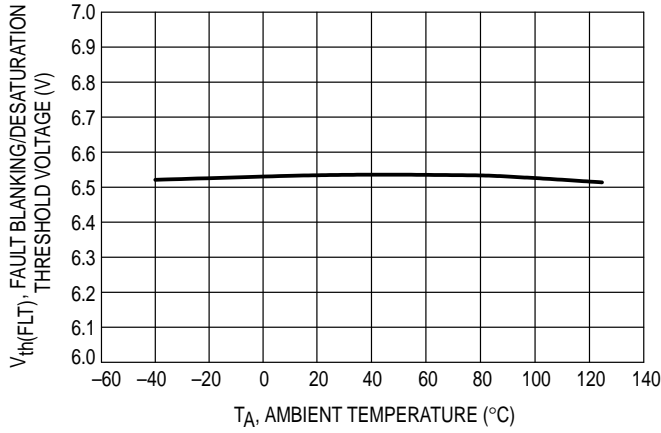


Figure 16. Blanking/Desaturation Threshold versus Supply Voltage

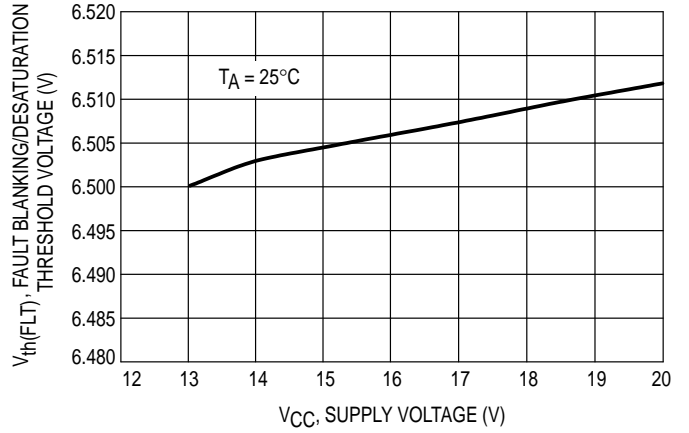


Figure 17. Blanking Current Source versus Temperature

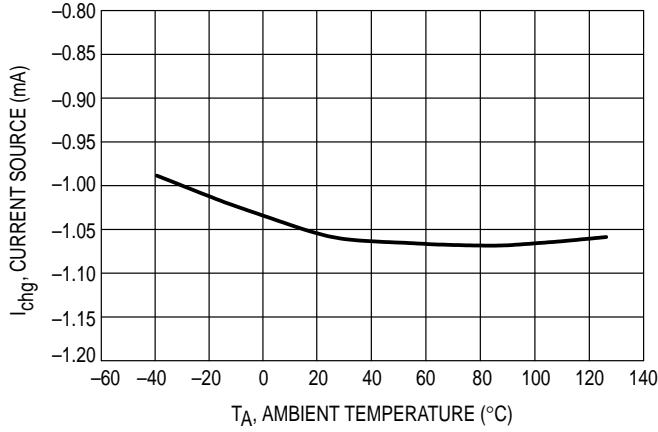


Figure 18. Blanking Current versus Supply Voltage

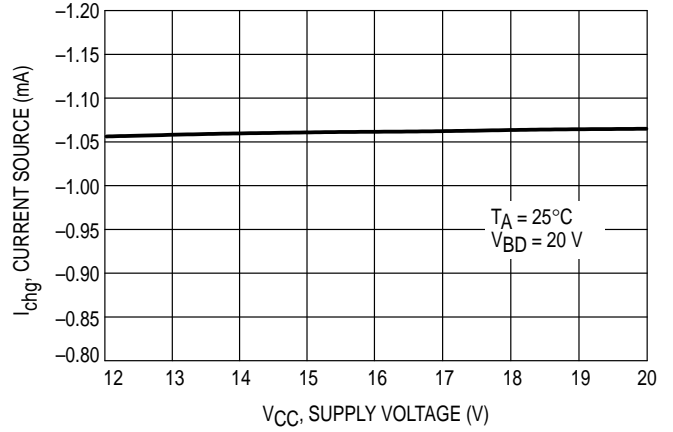


Figure 19. Blanking Current versus Blanking/Desaturation Voltage

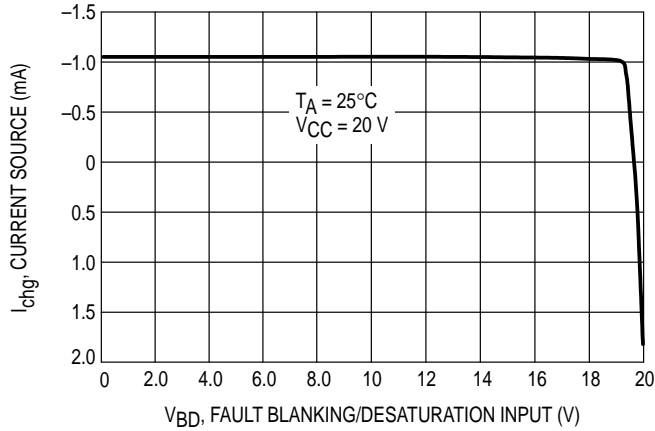


Figure 20. Blanking Discharge Current versus Blanking/Desaturation Voltage

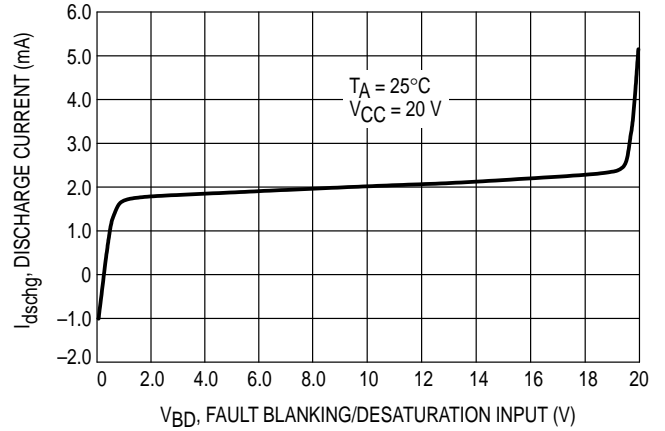


Figure 21. Fault Output Voltage Low versus Fault Output Current

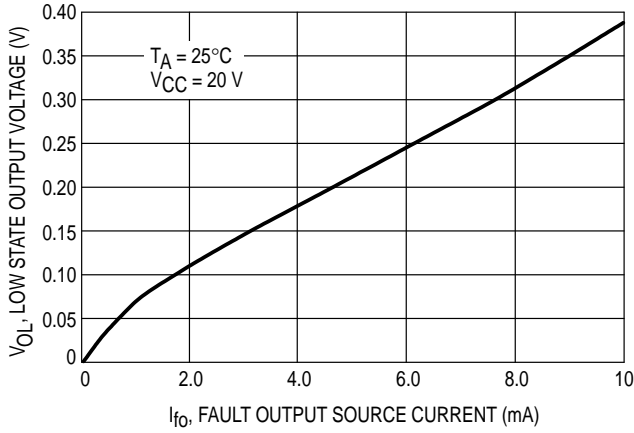


Figure 22. Fault Output Voltage High versus Fault Output Current

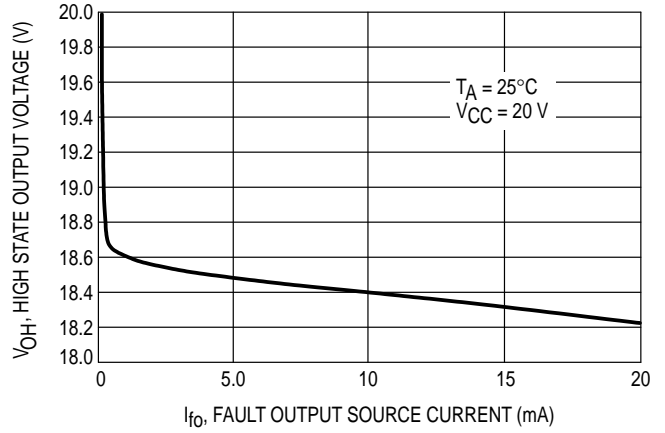


Figure 23. UVLO Start Threshold versus Temperature

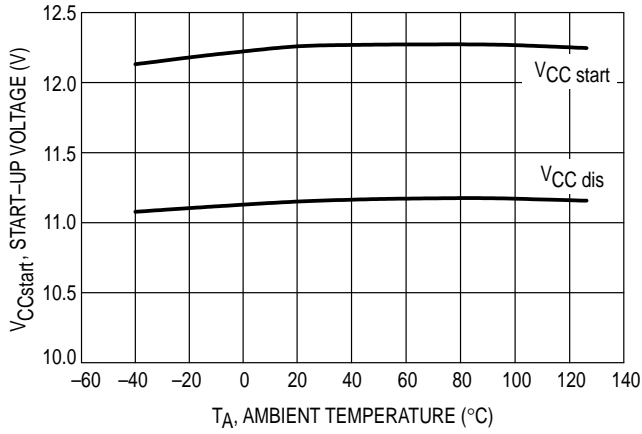


Figure 24. Standby Supply Current versus Supply Voltage

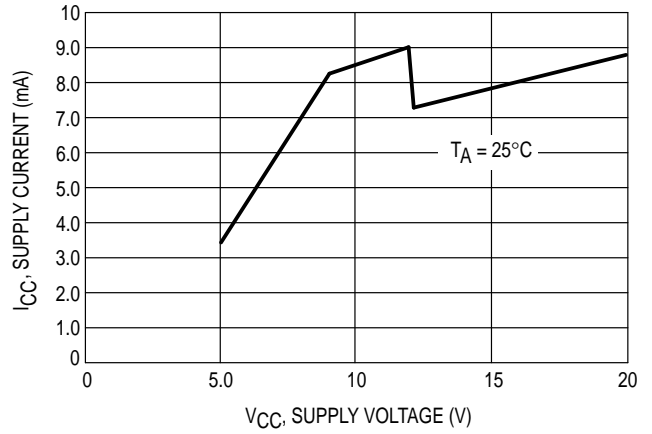
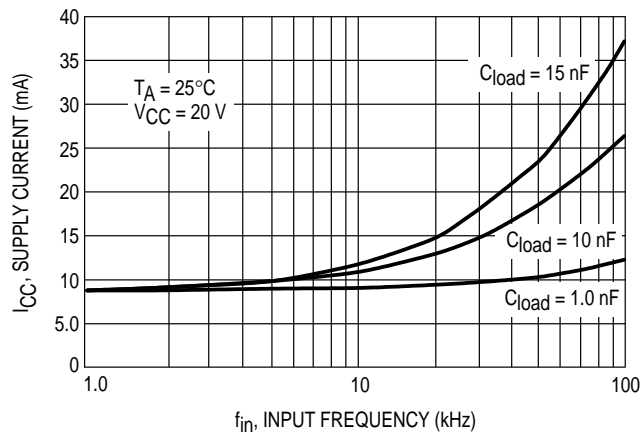


Figure 25. Supply Current versus Input Frequency



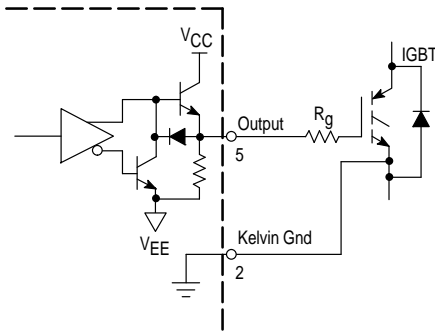
## GATE DRIVE

### Controlling Switching Times

The most important design aspect of an IGBT gate drive is optimization of the switching characteristics. Switching characteristics are especially important in motor control applications in which PWM transistors are used in a bridge configuration. In these applications, the gate drive circuit components should be selected to optimize turn-on, turn-off, and off-state impedance.

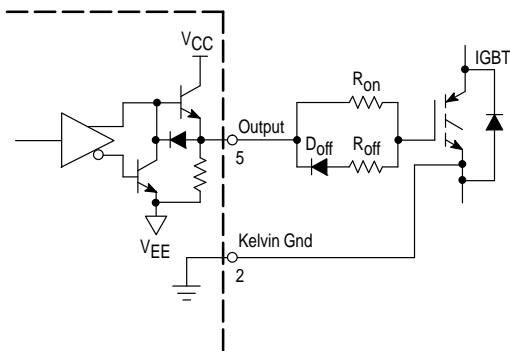
A single resistor may be used to control both turn-on and turn-off and shown in Figure 26. However, the resistor value selected must be a compromise in turn-on abruptness and turn-off losses. Using a single resistor is normally suitable only for very low frequency PWM.

Figure 26. Using a Single Gate Resistor



An optimized gate drive output stage is shown in Figure 27. This circuit allows turn-on and turn-off to be optimized separately.

Figure 27. Using Separate Resistors for Turn-On and Turn-Off



The turn-on resistor  $R_{on}$  provides control over the IGBT turn-on speed. In motor control circuits, the resistor sets the turn-on  $di/dt$  that controls how fast the free-wheel diode is cleared. The interaction of the IGBT and freewheeling diode determines the turn-on  $dv/dt$ .

Excessive turn-on  $dv/dt$  is a common problem in half-bridge circuits.

The turn-off resistor  $R_{off}$  controls the turn-off speed and ensures that the IGBT remains off under commutation stresses. Turn-off is critical to obtain low switching losses.

While IGBTs exhibit a fixed minimum loss due to minority carrier recombination, a slow gate drive will dominate the turn-off losses. This is particularly true for fast IGBTs. It is also possible to turn-off an IGBT too fast. Excessive turn-off speed will result in large overshoot voltages. Normally the turn-off resistor is a small fraction of the turn-on resistor.

The MC33154 has a bipolar totem pole output. The output stage is capable of sourcing 4.0 amps and sinking 2.0 amps peak. The output stage also contains a pull down resistor to ensure that the IGBT is off when the gate drive power is not applied.

In a PWM inverter, IGBTs are used in a half-bridge configuration. Thus, at least one device is always off. While the IGBT is in the off-state it will be subjected to changes in voltage caused by the other devices. This is particularly a problem when the opposite transistor turns on.

When the lower device is turned on clearing the upper diode, the turn-on  $dv/dt$  of the lower device appears across the collector emitter of the upper device. To eliminate shoot-through currents it is necessary to provide a low sink impedance to the device in the off-state. Fortunately, the turn-off resistor can be made small enough to hold off the device under commutation without causing excessively fast turn-off speeds.

Sometimes a negative bias voltage is used in the off-state. This is a practice carried over from bipolar Darlington drives. A negative bias is generally not required for IGBTs. However, a negative bias will reduce the possibility of shoot-through. The MC33154 has separate pins for  $V_{EE}$  and Kelvin Gnd. This permits operation using a +15/-5 volt supply.

## INTERFACING WITH OPTOISOLATORS

### Isolated Input

The MC33154 may be used with an optically isolated input. The optoisolator can be used to provide level shifting and if desired, isolation from AC line voltages. An optoisolator with a very high  $dv/dt$  capability should be used, such as the Hewlett-Packard HCPL0453. The IGBT gate turn-on resistor should be set large enough to ensure that the opto's  $dv/dt$  capability is not exceeded. Like most optoisolators, the HCPL0453 has an active low open-collector output. Thus, when the LED is ON, the output will be low. The MC33154 has a non-inverting input pin to interface directly with an optoisolator using a pull up resistor.

### Optoisolator Output Fault

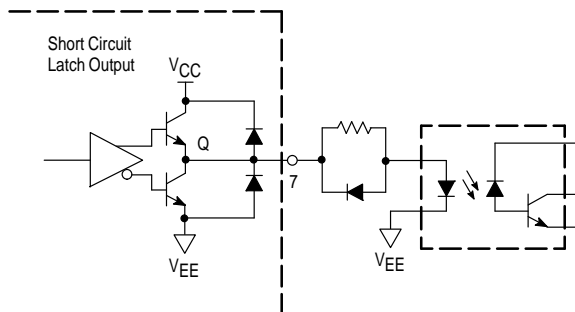
The MC33154 has an active high fault output. The fault output may be easily interfaced to an optoisolator. While it is important that all faults are properly reported, it is equally important that no false signals are propagated. Again a high  $dv/dt$  optoisolator should be used.

The LED drive provides a resistor programmable current of 10 to 20 mA when on and provides a low impedance path when off.



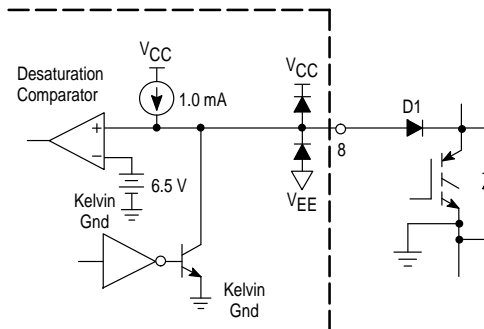
An active high output, resistor, and small signal diode provide an excellent LED driver. This circuit is shown in Figure 28.

Figure 28. Output Fault Optoisolator



voltage on the desaturation input. The voltage reference is set to about 6.5 V. This will allow a maximum ON-voltage of about 5.0 V.

Figure 29. Desaturation Detection Using a Diode



## UNDER VOLTAGE LOCK OUT

It is desirable to protect an IGBT from insufficient gate voltage. IGBTs require 15 V on the gate to guarantee device saturation. At gate voltages below 13 V, the “on” state voltage increases dramatically, especially at higher currents. At very lower gate voltages, below 10 V, the IGBT may operate in the linear region and quickly overheat. Many PWM motor drives use a bootstrap supply for the upper gate drive. The UVLO provides protection for the IGBT in case the bootstrap capacitor discharges.

The MC33154 will typically start up at about 12 V. The UVLO circuit has about 1.0 volt of hysteresis. The UVLO will disable the output if the supply voltage falls below about 11 V.

## PROTECTION CIRCUITRY

### Desaturation Protection

Bipolar Power circuits have commonly used what is known as “Desaturation Detection”. This involves monitoring the collector voltage and turning off the device if the collector voltage rises above a certain limit. A bipolar transistor will only conduct a certain amount of current for a given base drive. When the base is overdriven the device is in saturation. When the collector current rises above the knee, the device pulls out of saturation.

The maximum current the device will conduct in the linear region is a function of the base current and  $h_{fe}$  of the transistor.

The output characteristics of an IGBT are similar to a Bipolar device. However the output current is a function of gate voltage, not current. The maximum current depends on the gate voltage and the device. IGBTs tend to have a very high transconductance and a much higher current density under a short circuit than a bipolar device.

Motor control IGBTs are designed for a lower current density under shorted conditions and a longer short circuit survival time.

The best method for detecting desaturation is the use of a high voltage clamp diode and a comparator. The MC33154 has a desaturation comparator which senses the collector voltage and provides an output indicating when the device is not full saturated. Diode D1 is an external high voltage diode with a rated voltage comparable to the power device. When the IGBT is ON and saturated, diode D1 will pull down the voltage on the desaturation input. When the IGBT is OFF or pulls out of saturation, the current source will pull up the

A fault exists when the gate input is high and  $V_{CE}$  of the IGBT is greater than the maximum allowable  $V_{CE(sat)}$ . The output of the desaturation comparator is ANDed with the gate input signal and fed into the Short Circuit (SC) latch. The SC latch will turn-off the IGBT for the remainder of the cycle when a fault is detected. When the input is toggled low, the latch will reset. The reference voltage is tied to the Kelvin Ground instead of the  $V_{EE}$  to make the threshold independent of negative gate bias.

The MC33154 also features a programmable turn-on blanking time. During turn-on the IGBT must clear the opposing free wheeling diode. The collector voltage will remain high until the diode is cleared. Once the diode has been cleared the voltage will come down quickly to the  $V_{CE(sat)}$  of the device. Following turn-on there is normally considerable ringing on the collector due to the  $C_{OSS}$  of the IGBTs and the parasitic wiring inductance.

The error signal from the desaturation signal must be blanked out sufficiently to allow the diode to be cleared and the ringing to settle out.

The blanking function uses an NPN transistor to clamp the comparator input when the gate input is low. When the input is switched high, the clamp transistor will turn-off, and the current source will charge up the blanking capacitor. The time required for blanking capacitor to charge up from the on-voltage of the clamp FET to the trip voltage of the comparator is the blanking time.

If a short circuit occurs after the IGBT is turned on and saturated, the delay time will be the time required for the current source to charge up the blanking capacitor from the  $V_{CE(sat)}$  to the trip voltage of the comparator.

### Sense IGBT Protection

Another approach to protecting the IGBTs is to sense the emitter current using a current shunt or Sense IGBTs.

This method has the advantage of being able to use high gain IGBTs which do not have any inherent short circuit capability.

Current sense IGBTs work as well as current sense MOSFETs in most circumstances. However, the basic problem of working with very low sense voltages still exists. Sense IGBTs sense current through the channel and are therefore linear concerning collector current.

Because IGBTs have a very low incremental on-resistance, sense IGBTs behave much like low-on resistance current sense MOSFETs. The output voltage of a

## MC33154

properly terminated sense IGBT is very low, normally less than 100 mV.

The sense IGBT approach requires a blanking time to prevent false tripping during turn-on. The sense IGBT also requires that the sense signal is ignored while the gate is low. This is because the mirror normally produces large transient voltages during both turn-on and turn-off due to the collector to mirror capacitance.

A low resistance current shunt may also be used to sense the emitter current. A very low resistance shunt (5.0 mΩ to 50 mΩ) must be used with high current IGBTs. The output voltage of a current shunt is also very low.

When the output is an actual short circuit the inductance will be very low. Since the blanking circuit provides a fixed minimum on-time the peak current under a short circuit may be very high. A short circuit discern function may be implemented using a second comparator with a higher trip voltage.

This circuit can distinguish between an overcurrent and a shorted output condition. Under an actual short circuit the die temperature may get very hot. When a short circuit is detected the transistor should be turned-off for several milliseconds to cool down before the device is turned back on.

The sense circuit is very similar to the Desaturation circuit. The MC33154 uses a combination circuit that provides protection for both Short Circuit capable IGBTs and Sense IGBTs.

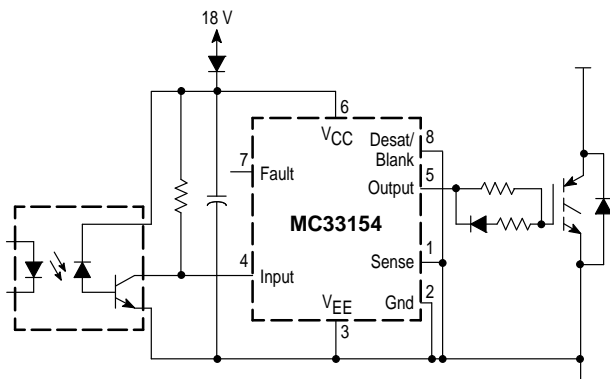
### APPLICATION EXAMPLES

The simplest gate drive circuit using the MC33154 is shown in Figure 30. The optoisolator requires a pull up resistor. This resistor value should be set to bias the output transistor at the desired current. A decoupling capacitor should be placed close to the IC to minimize switching noise.

A bootstrap diode may be used to for a floating supply. If the protection features are not used, then both the desaturation input and the current sense input should be grounded.

When used with a single supply the Kelvin Gnd and  $V_{EE}$  pins should be connected. Separate resistors are recommended for turn-on and turn-off.

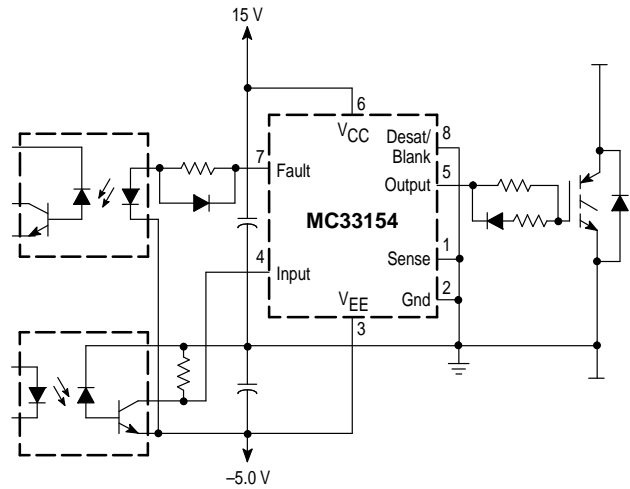
**Figure 30. Basic Application**



When used with a dual supply as shown in Figure 31, the Gnd pin should be Kelvin connected to the emitter of the IGBT. If the protection features are not used, then both the desaturation input and the current sense input should be

connected to Gnd. The input optoisolator, however, should be referenced to  $V_{EE}$ .

**Figure 31. Dual Supply Application**

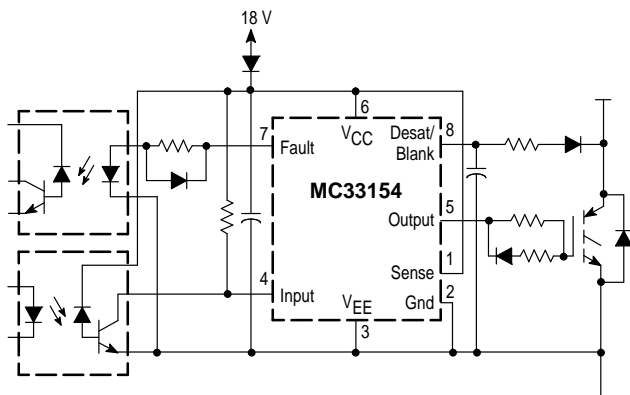


If Desaturation protection is desired as shown in Figure 32, a high voltage diode is connected to the Desaturation/Blanking pin. The blanking capacitor should be connected from the Desaturation pin to the  $V_{EE}$  pin. If a dual supply is used the blanking capacitor should be connected to the Kelvin Gnd.

Because desaturation protection is used in this example, the sense input should be tied high. The MC33154 design ANDs the output of the overcurrent comparators with the output of the desaturation comparator, allowing the circuit designer to choose either type of protection.

Although the reverse voltage on collector of the IGBT is clamped to the emitter by the free wheeling diode, there is normally considerable inductance within the package itself. A small resistor in series with the diode may be used to protect the IC from reverse voltage transients.

**Figure 32. Desaturation Application**



When using sense IGBTs or a sense resistor, as shown in Figure 33, the sense voltage is applied to the current sense input. The sense trip voltages are referenced to the Kelvin Gnd pin. The sense voltage is very small, typically about 65 mV, and sensitive to noise.

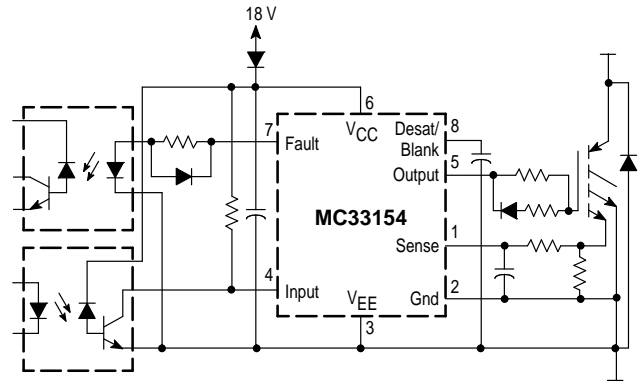
Therefore, the sense and ground return conductors should be routed as a differential pair. An RC filter is useful in filtering any high frequency noise. A blanking capacitor is connected


## MC33154

from the blanking pin to  $V_{EE}$ . The stray capacitance on the blanking pin provides a very small level of blanking if left open.

The blanking pin should not be grounded when using current sensing. That would disable the overcurrent sense. The blanking pin should never be tied high. That would short out the internal IC clamp transistor.

Figure 33. Sense IGBT Application

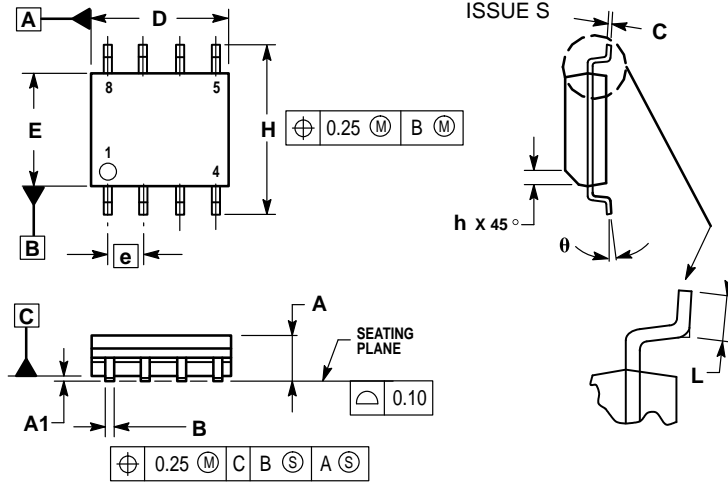


Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and  are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

# MC33154

## OUTLINE DIMENSIONS

### D SUFFIX PLASTIC PACKAGE CASE 751-05 ISSUE S

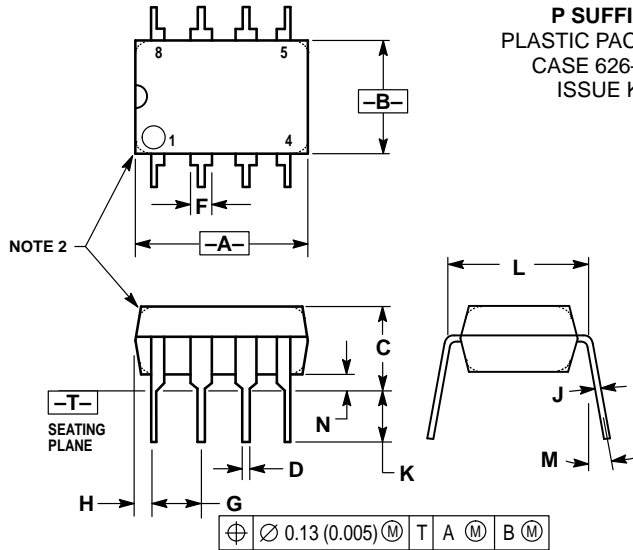


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSION D AND E DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
5. DIMENSION B DOES NOT INCLUDE MOLD PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL CONDITION.

| DIM      | MILLIMETERS |      |
|----------|-------------|------|
|          | MIN         | MAX  |
| A        | 1.35        | 1.75 |
| A1       | 0.10        | 0.25 |
| B        | 0.35        | 0.49 |
| C        | 0.18        | 0.25 |
| D        | 4.80        | 5.00 |
| E        | 3.80        | 4.00 |
| e        | 1.27 BSC    |      |
| H        | 5.80        | 6.20 |
| h        | 0.25        | 0.50 |
| L        | 0.40        | 1.25 |
| $\theta$ | 0°          | 7°   |

### P SUFFIX PLASTIC PACKAGE CASE 626-05 ISSUE K



NOTES:

1. DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
2. PACKAGE CONTOUR OPTIONAL (ROUND OR SQUARE CORNERS).
3. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

| DIM | MILLIMETERS |       | INCHES    |       |
|-----|-------------|-------|-----------|-------|
|     | MIN         | MAX   | MIN       | MAX   |
| A   | 9.40        | 10.16 | 0.370     | 0.400 |
| B   | 6.10        | 6.60  | 0.240     | 0.260 |
| C   | 3.94        | 4.45  | 0.155     | 0.175 |
| D   | 0.38        | 0.51  | 0.015     | 0.020 |
| F   | 1.02        | 1.78  | 0.100 BSC |       |
| G   | 2.54 BSC    |       | 0.100 BSC |       |
| H   | 0.76        | 1.27  | 0.030     | 0.050 |
| J   | 0.20        | 0.30  | 0.008     | 0.012 |
| K   | 2.92        | 3.43  | 0.115     | 0.135 |
| L   | 7.62 BSC    |       | 0.300 BSC |       |
| M   | — 10°       |       | — 10°     |       |
| N   | 0.76        | 1.01  | 0.030     | 0.040 |

STYLE 1:

1. AC IN
2. DC + IN
3. DC - IN
4. AC IN
5. GROUND
6. OUTPUT
7. AUXILIARY
8. V<sub>CC</sub>

How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution;  
P.O. Box 5405, Denver, Colorado 80217. 1-303-675-2140 or 1-800-441-2447

JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 141,  
4-32-1 Nishi-Gotanda, Shagawa-ku, Tokyo, Japan. 03-5487-8488

Customer Focus Center: 1-800-521-6274

Mfax™: RMFAX0@email.sps.mot.com – TOUCHTONE 1-602-244-6609  
Motorola Fax Back System – US & Canada ONLY 1-800-774-1848  
– http://sps.motorola.com/mfax/

ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,  
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

HOME PAGE: <http://motorola.com/sps/>

Mfax is a trademark of Motorola, Inc.

